AMENDMENTS TO THE CLAIMS

Listing of the Claims:

Claims 1-7 (Canceled).

8. (Currently Amended) A semiconductor device with a trench isolation, comprising:

a silicon substrate having a trench on a surface thereof;

a filling layer positioned in the trench for device isolation; and

a silicon oxide layer containing fluorine ~~healing elements~~ positioned between the filling layer and the silicon substrate.

9. (Currently Amended) The semiconductor device with a trench isolation as claimed in claim 8, wherein the fluorine is ~~healing elements are~~ contained in an interface boundary between the silicon oxide layer and the substrate.

10. (Original) The semiconductor device with a trench isolation as claimed in claim 8, further comprising a silicon nitride layer as an oxide barrier layer between the silicon oxide layer and the filling layer.

11. (Currently Amended) The semiconductor device with a trench isolation as claimed in claim 8, wherein the filling layer comprises a spin-on-glass oxide layer or a CVD silicon oxide layer.

Claims 12-31 (Canceled).